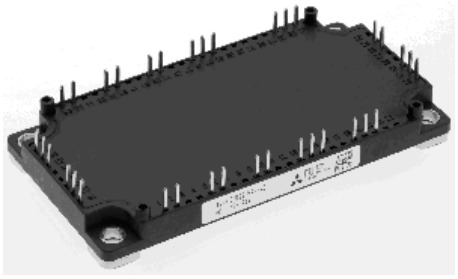
CM75MXA-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

CM75MXA-24S **- 6th Generation NX series -**



Collector current I_C ..... **7 5** A

Collector-emitter voltage V_{CES} ..... **1 2 0 0** V

- ●Flat base Type
- ●Copper base plate (non-plating)
- ●Tin plating pin terminals
- ●RoHS Directive compliant
- ●UL Recognized under UL1557, File E323585

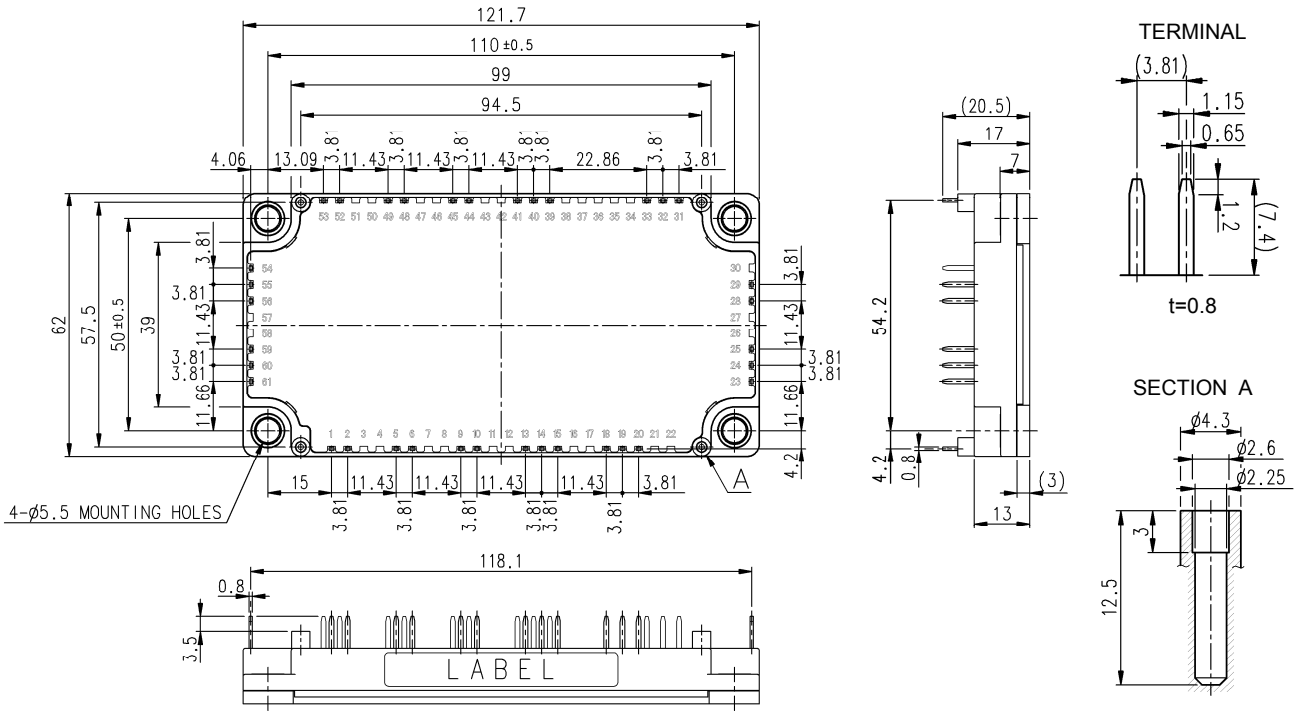
CIB (Converter+Inverter+BrakeCopper)

APPLICATION

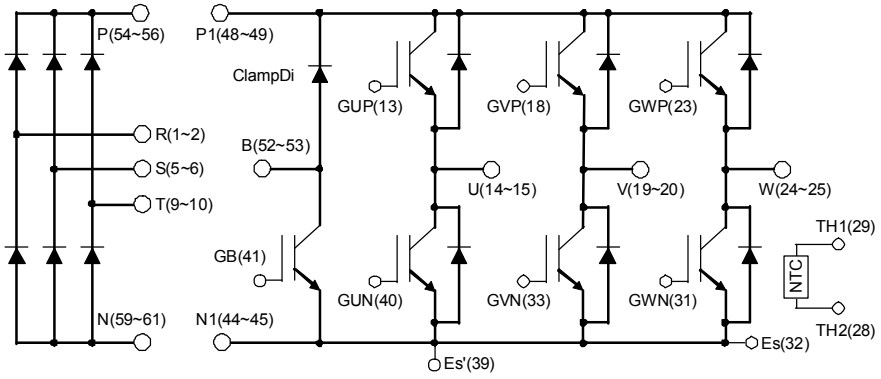
AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



INTERNAL CONNECTION



Caution: Each (two or three) pin terminal of P/N/R/S/T/P1/N1/U/V/W/B is connected in the module, but should use all each three pins for the external wiring.

Tolerance otherwise specified

Division of Dimension		Tolerance
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

The tolerance of size between terminals is assumed to be ±0.4.

MITSUBISHI ELECTRIC

ABSOLUTE MAXIMUM RATINGS (T_j=25 °C, unless otherwise specified)

Inverter part IGBT/FWDi

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	±20	V
I_C	Collector current	DC, T_C=122 °C (Note.2, 4)	75	A
I_{CRM}		Pulse (Note.3)	150	
P_{tot}	Total power dissipation	T_C=25 °C (Note.2, 4)	600	W
I_E (Note.1)	Emitter current	T_C=25 °C (Note.2, 4)	75	A
I_{ERM} (Note.1)		Pulse (Note.3)	150	
T_{jmax}	Maximum junction temperature	-	175	°C

Brake part IGBT/ClampDi

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	±20	V
I_C	Collector current	DC, T_C=125 °C (Note.2)	50	A
I_{CRM}		Pulse (Note.3)	100	
P_{tot}	Total power dissipation	T_C=25 °C (Note.2, 4)	425	W
V_{RRM}	Repetitive peak reverse voltage	G-E short-circuited	1200	V
I_F (Note.1)	Forward current	T_C=25 °C (Note.2, 4)	50	A
I_{FRM} (Note.1)		Pulse (Note.3)	100	
T_{jmax}	Maximum junction temperature	-	175	°C

Converter part ConvDi

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	-	1600	V
E_a	Recommended AC input voltage	RMS	440	V
I_O	DC output current	3-phase full wave rectifying, T_C=125 °C (Note.2)	75	A
I_{FSM}	Surge forward current	The sine half wave 1 cycle peak value, f=60 Hz, non-repetitive	750	A
I^2t	Current square time	Value for one cycle of surge current	2340	A^2s
T_{jmax}	Maximum junction temperature	-	150	°C

Module

Symbol	Item	Conditions	Rating	Unit
T_{Cmax}	Maximum case temperature	(Note.2)	125	°C
T_{jop}	Operating junction temperature	-	-40 ~ +150	°C
T_{stg}	Storage temperature	-	-40 ~ +125	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
d_s	Creepage distance	Terminal to terminal	6.47	-	-	mm
		Terminal to base plate	14.27	-	-	
d_a	Clearance	Terminal to terminal	6.47	-	-	mm
		Terminal to base plate	12.33	-	-	
m	Weight	-	-	300	-	g
e_c	Flatness of base plate	On the centerline X, Y (Note.5)	±0	-	+100	μm

ELECTRICAL CHARACTERISTICS (T_j=25 °C, unless otherwise specified)

Inverter part IGBT/FWDi

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	0.5	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=7.5 mA, V_{CE}=10 V		5.4	6.0	6.6	V
V_{CEsat} (Terminal)	Collector-emitter saturation voltage	I_C=75 A (Note.6), V_{GE}=15 V	T_j=25 °C	-	1.80	2.25	V
			T_j=125 °C	-	2.00	-	
			T_j=150 °C	-	2.05	-	
V_{CEsat} (Chip)	Collector-emitter saturation voltage	I_C=75 A (Note.6), V_{GE}=15 V	T_j=25 °C	-	1.70	2.15	V
			T_j=125 °C	-	1.90	-	
			T_j=150 °C	-	1.95	-	
C_{ies}	Input capacitance	V_{CE}=10 V, G-E short-circuited		-	-	7.5	nF
C_{oes}	Output capacitance			-	-	1.5	
C_{res}	Reverse transfer capacitance			-	-	0.13	
Q_G	Gate charge	V_{CC}=600 V, I_C=75 A, V_{GE}=15 V		-	175	-	nC
$t_{d(on)}$	Turn-on delay time	V_{CC}=600 V, I_C=75 A, V_{GE}=±15 V, R_G=8.2 Ω, Inductive load		-	-	300	ns
t_r	Rise time			-	-	200	
$t_{d(off)}$	Turn-off delay time			-	-	600	
t_f	Fall time			-	-	300	
V_{EC} (Note.1) (Terminal)	Emitter-collector voltage	I_E=75 A (Note.6), G-E short-circuited	T_j=25 °C	-	1.8	2.25	V
			T_j=125 °C	-	1.8	-	
			T_j=150 °C	-	1.8	-	
V_{EC} (Note.1) (Chip)	Emitter-collector voltage	I_E=75 A (Note.6), G-E short-circuited	T_j=25 °C	-	1.7	2.15	V
			T_j=125 °C	-	1.7	-	
			T_j=150 °C	-	1.7	-	
t_{rr} (Note.1)	Reverse recovery time	V_{CC}=600 V, I_E=75 A, V_{GE}=±15 V, R_G=8.2 Ω, Inductive load		-	-	300	ns
Q_{rr} (Note.1)	Reverse recovery charge			-	4.0	-	μC
E_{on}	Turn-on switching energy per pulse	V_{CC}=600 V, I_C=I_E=75 A, V_{GE}=±15 V, R_G=8.2 Ω, T_j=150 °C, Inductive load		-	7.3	-	mJ
E_{off}	Turn-off switching energy per pulse			-	8.0	-	
E_{rr} (Note.1)	Reverse recovery energy per pulse			-	6.9	-	mJ
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, T_C=25 °C (Note.2)		-	-	4.0	mΩ
r_g	Internal gate resistance	Per switch		-	0	-	Ω

Brake part IGBT/ClampDi

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	0.5	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=5 mA, V_{CE}=10 V		5.4	6.0	6.6	V
V_{CEsat} (Terminal)	Collector-emitter saturation voltage	I_C=50 A (Note.6), V_{GE}=15 V	T_j=25 °C	-	1.80	2.25	V
			T_j=125 °C	-	2.00	-	
			T_j=150 °C	-	2.05	-	
V_{CEsat} (Chip)	Collector-emitter saturation voltage	I_C=50 A (Note.6), V_{GE}=15 V	T_j=25 °C	-	1.70	2.15	V
			T_j=125 °C	-	1.90	-	
			T_j=150 °C	-	1.95	-	
C_{ies}	Input capacitance	V_{CE}=10 V, G-E short-circuited		-	-	5.0	nF
C_{oes}	Output capacitance			-	-	1.0	
C_{res}	Reverse transfer capacitance			-	-	0.08	
Q_G	Gate charge	V_{CC}=600 V, I_C=50 A, V_{GE}=15 V		-	117	-	nC

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified)

Brake part IGBT/ClampDi

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time	V_{CC}=600 V, I_C=50 A, V_{GE}=±15 V, R_G=13 Ω, Inductive load		-	-	300	ns
t_r	Rise time			-	-	200	
$t_{d(off)}$	Turn-off delay time			-	-	600	
t_f	Fall time			-	-	300	
I_{RRM}	Repetitive peak reverse current	V_R=V_{RRM}, G-E short-circuited		-	-	1	mA
V_F (Terminal)	Forward voltage	I_F=50 A (Note.6), G-E short-circuited	T_j=25 °C	-	1.8	2.25	V
			T_j=125 °C	-	1.8	-	
			T_j=150 °C	-	1.8	-	
V_F (Chip)	Forward voltage	I_F=50 A (Note.6), G-E short-circuited	T_j=25 °C	-	1.7	2.15	V
			T_j=125 °C	-	1.7	-	
			T_j=150 °C	-	1.7	-	
t_{rr}	Reverse recovery time	V_{CC}=600 V, I_F=50 A, V_{GE}=±15 V, R_G=13 Ω, Inductive load		-	-	300	ns
Q_{rr}	Reverse recovery charge			-	2.7	-	µC
E_{on}	Turn-on switching energy per pulse	V_{CC}=600 V, I_C=I_F=50 A, V_{GE}=±15 V, R_G=13 Ω, T_j=150 °C, Inductive load		-	5.5	-	mJ
E_{off}	Turn-off switching energy per pulse			-	5.3	-	
E_{rr}	Reverse recovery energy per pulse			-	4.5	-	mJ
r_g	Internal gate resistance	-		-	0	-	Ω

Converter part ConvDi

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{RRM}	Repetitive peak reverse current	V_R=V_{RRM}, T_j=150 °C	-	-	20	mA
V_F (Terminal)	Forward voltage	I_F=75 A (Note.6)	-	1.2	1.6	V

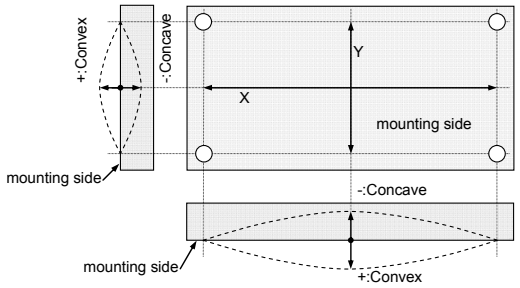
NTC thermistor part

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero power resistance	T_C=25 °C (Note.2)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	T_C=100 °C, R_{100}=493 Ω	-7.3	-	+7.8	%
$B_{(25/50)}$	B constant	Approximate by equation (Note.7)	-	3375	-	K
P_{25}	Power dissipation	T_C=25 °C (Note.2)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance (Note. 2)	Junction to case, per Inverter IGBT	-	-	0.25	K/W
$R_{th(j-c)D}$		Junction to case, per Inverter FWDi	-	-	0.40	
$R_{th(j-c)Q}$		Junction to case, per Brake IGBT	-	-	0.35	K/W
$R_{th(j-c)D}$		Junction to case, per Brake ClampDi	-	-	0.63	
$R_{th(j-c)D}$		Junction to case, per ConvDi	-	-	0.24	K/W
$R_{th(c-s)}$	Contact thermal resistance (Note. 2)	Case to heat sink, per 1 module, Thermal grease applied (Note.8)	-	15	-	K/kW

Note.1: Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).
Note.2: Case temperature (T_C) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
Note.3: Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.
Note.4: Junction temperature (T_j) should not increase beyond T_{jmax} rating.
Note.5: The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



Note.6: Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

Note.7: $B_{(25/50)} = \ln(\frac{R_{25}}{R_{50}}) / (\frac{1}{T_{25}} - \frac{1}{T_{50}})$,

R_{25}: resistance at absolute temperature T_{25} [K]; T_{25}=25 [°C]+273.15=298.15 [K]
R_{50}: resistance at absolute temperature T_{50} [K]; T_{50}=50 [°C]+273.15=323.15 [K]

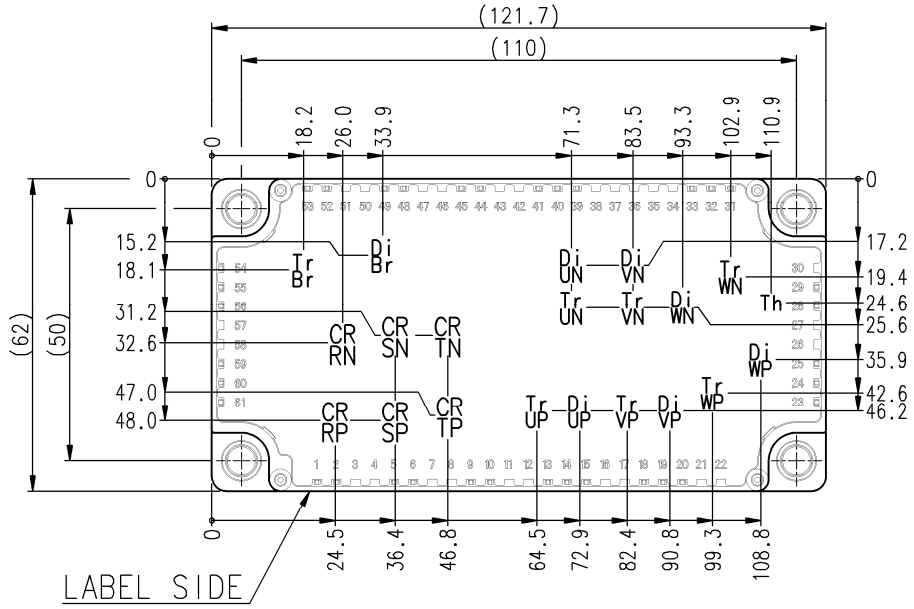
Note.8: Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).
Note.9: Japan Electronics and Information Technology Industries Association (JEITA) standards, "EIAJ ED-4701/300: Environmental and endurance test methods for semiconductor devices (Stress test I)"
Note.10: Use the following screws when mounting the printed circuit board (PCB) on the stand offs. "M2.6×10 or M2.6×12 self tapping screw" The length of the screw depends on the thickness of the PCB.

RECOMMENDED OPERATING CONDITIONS (T_a=25 °C)

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
V_{CC}	DC supply voltage	Applied across P1(P)-N1(N) terminals		-	600	850	V
V_{GEon}	Gate-emitter drive voltage	Applied across GB-Es/ G*P-*/G*N-Es (*=U,V,W) terminals		13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	Inverter IGBT	8.2	-	82	Ω
			Brake IGBT	13	-	130	

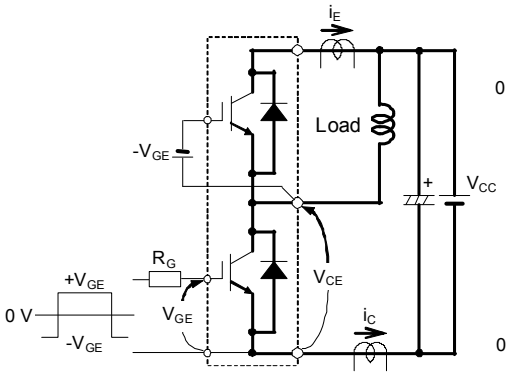
CHIP LOCATION (top view)

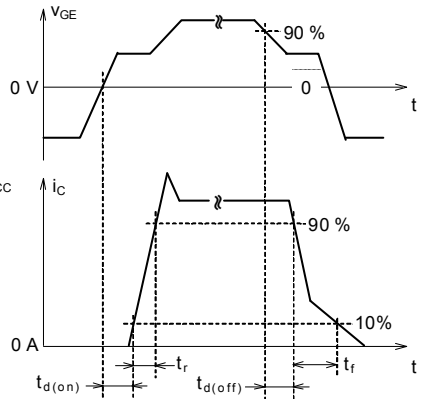
Dimension in mm, Tolerance: ±1 mm



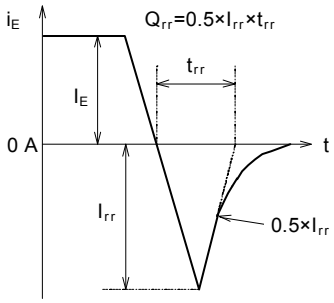
Tr*P/Tr*N/TrBr: IGBT, Di*P/Di*N: FWDi (*=U/V/W), DiBr: ClampDi, CR*P/CR*N: ConvDi (*=R/S/T), Th: NTC thermistor
Each mark points the center position of each chip or device.

TEST CIRCUIT AND WAVEFORMS

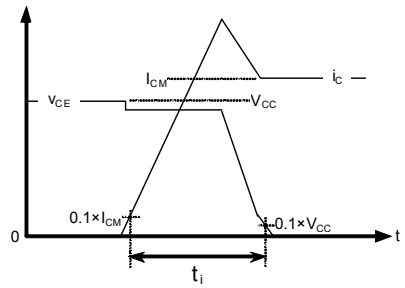




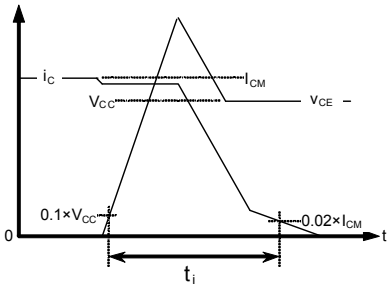
Switching characteristics test circuit and waveforms



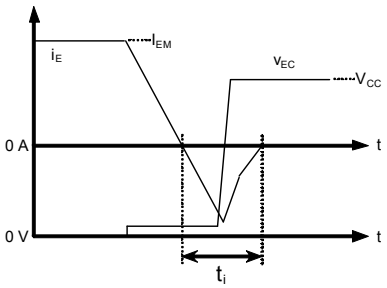
t_{rr}, Q_{rr} test waveform



IGBT Turn-on switching energy



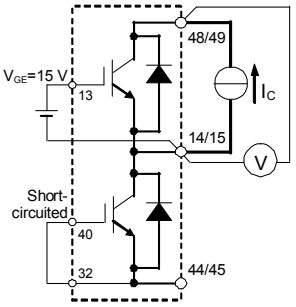
IGBT Turn-off switching energy



FWDi reverse recovery energy

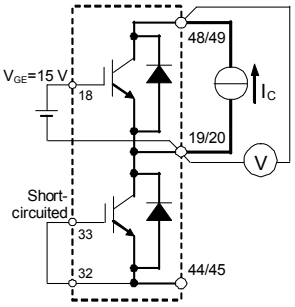
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT



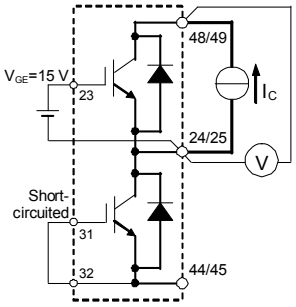
G-E short-circuited
GVP-V, GVN-Es, GWP-W, GWN-Es, GB-Es

UP / UN IGBT



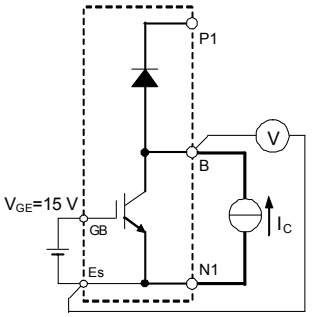
G-E short-circuited
GUP-U, GUN-Es, GWP-W, GWN-Es, GB-Es

VP / VN IGBT



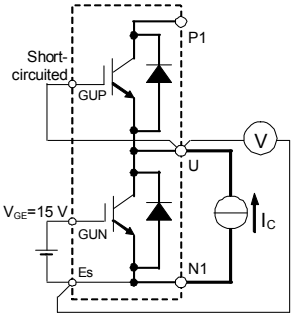
G-E short-circuited
GUP-U, GUN-Es, GVP-V, GVN-Es, GB-Es

WP / WN IGBT



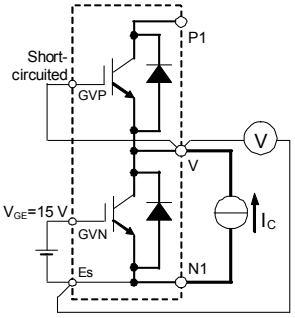
G-E short-circuited
GUP-U, GUN-Es, GVP-V, GVN-Es, GWP-W, GWN-Es

Brake IGBT / ClampDi



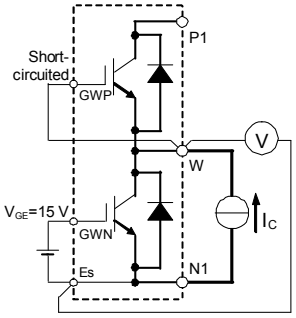
G-E short-circuited
GVP-V, GVN-Es, GWP-W, GWN-Es, GB-Es

UP / UN IGBT



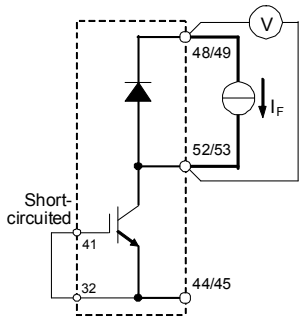
G-E short-circuited
GUP-U, GUN-Es, GWP-W, GWN-Es, GB-Es

VP / VN IGBT



G-E short-circuited
GUP-U, GUN-Es, GVP-V, GVN-Es, GB-Es

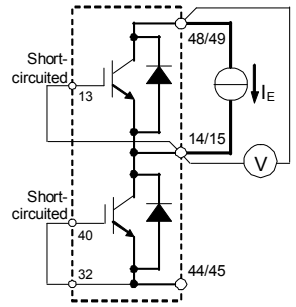
WP / WN IGBT



G-E short-circuited
GUP-U, GUN-Es, GVP-V, GVN-Es, GWP-W, GWN-Es

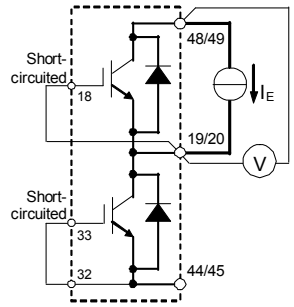
Brake IGBT / ClampDi

V_{CEsat} / ClampDi V_F test circuit



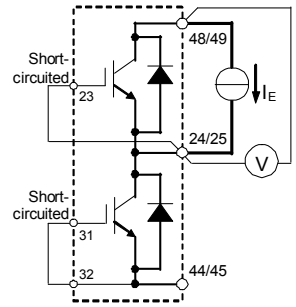
G-E short-circuited
GVP-V, GVN-Es, GWP-W, GWN-Es, GB-Es

UP / UN FWDi



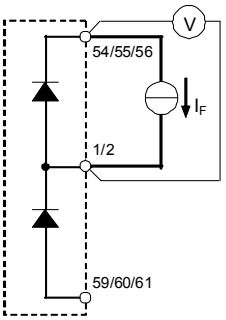
G-E short-circuited
GUP-U, GUN-Es, GWP-W, GWN-Es, GB-Es

VP / VN FWDi

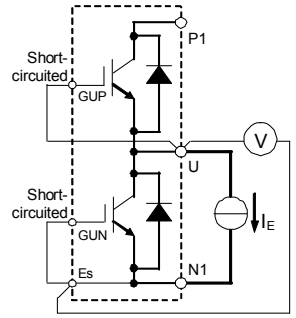


G-E short-circuited
GUP-U, GUN-Es, GVP-V, GVN-Es, GB-Es

WP / WN FWDi

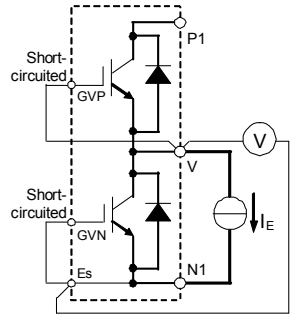


ConvDi (ex. phase-R)



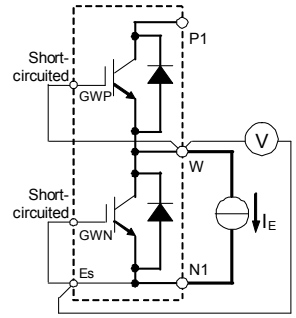
G-E short-circuited
GVP-V, GVN-Es, GWP-W, GWN-Es, GB-Es

UP / UN FWDi



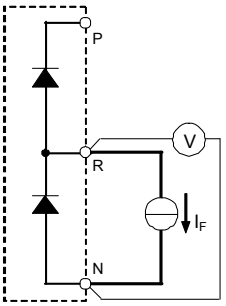
G-E short-circuited
GUP-U, GUN-Es, GWP-W, GWN-Es, GB-Es

VP / VN FWDi



G-E short-circuited
GUP-U, GUN-Es, GVP-V, GVN-Es, GB-Es

WP / WN FWDi



ConvDi (ex. phase-R)

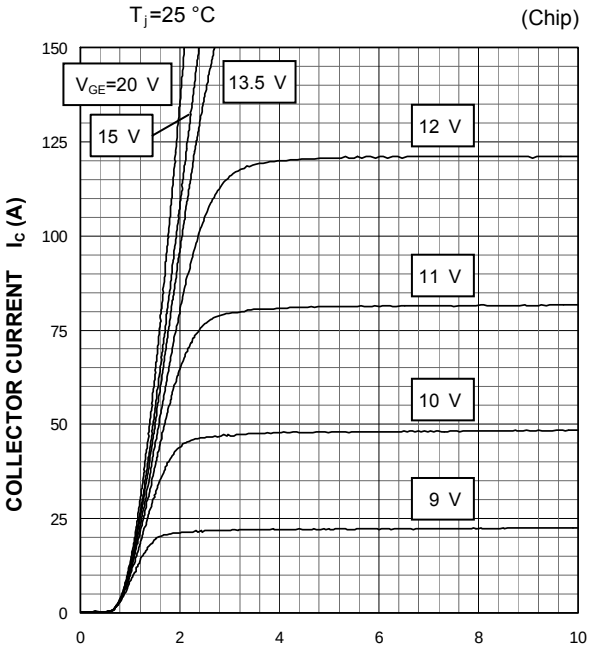
V_{EC} / ConvDi V_F test circuit

* In case of the above example, P1/N1/U/V/W should use all each three pin terminals for the external wiring.

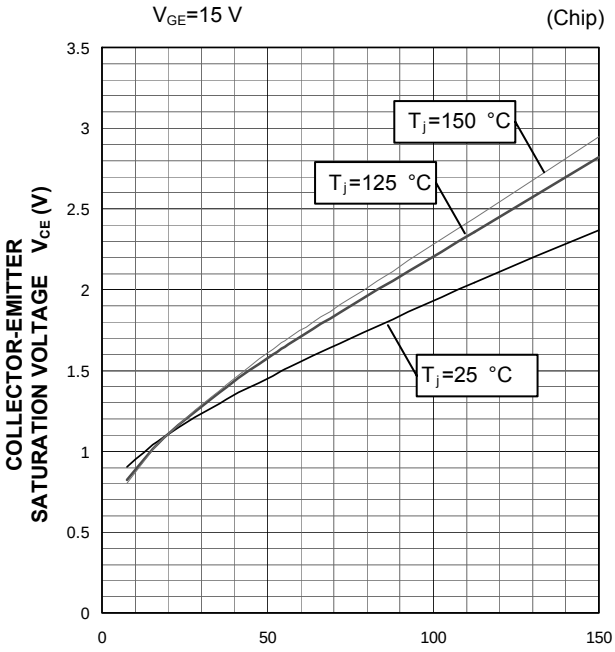
PERFORMANCE CURVES

INVERTER PART

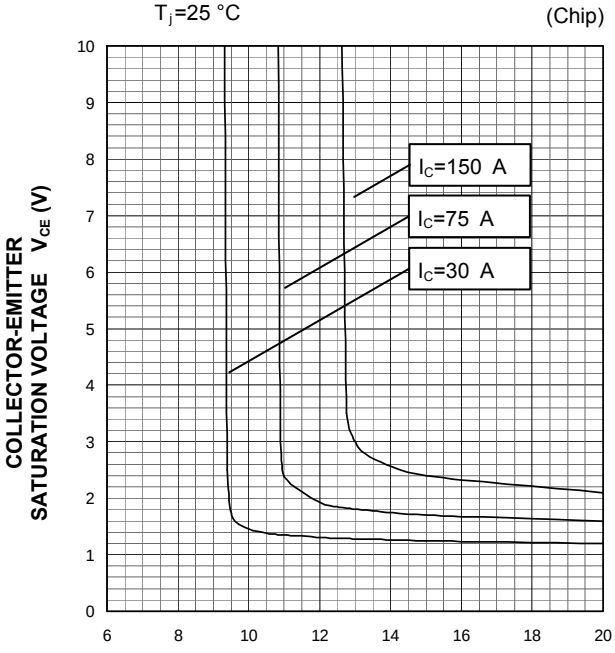
OUTPUT CHARACTERISTICS (TYPICAL)



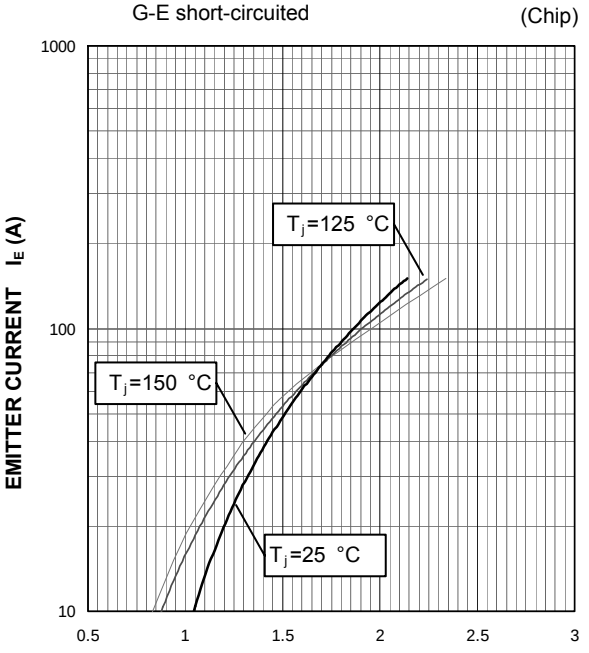
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

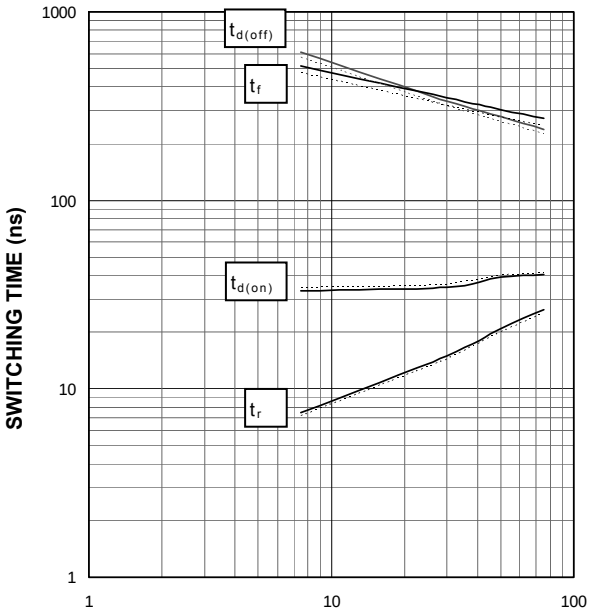


FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

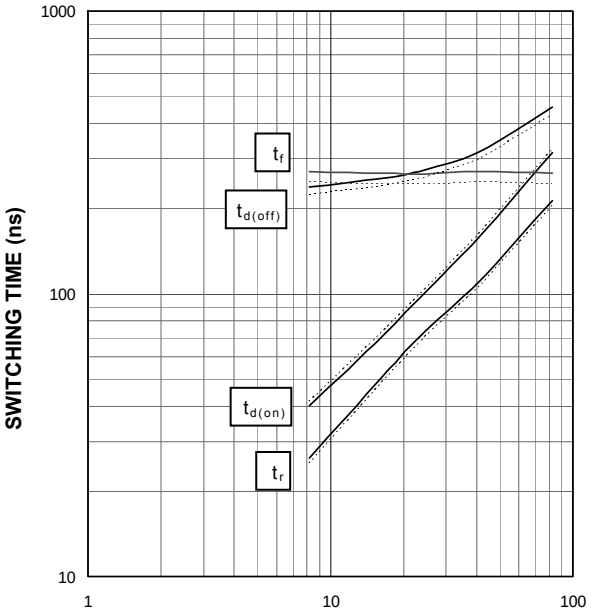
V_{CC}=600 V, V_{GE}=±15 V, R_G=8.2 Ω,
——————: T_j=150 °C, - - - - -: T_j=125 °C



COLLECTOR CURRENT I_C (A)

HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

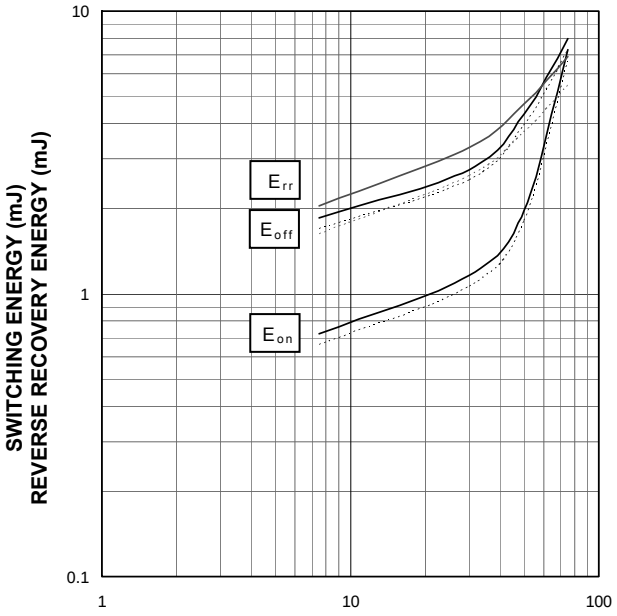
V_{CC}=600 V, V_{GE}=±15 V, I_C=75 A,
——————: T_j=150 °C, - - - - -: T_j=125 °C



EXTERNAL GATE RESISTANCE R_G (Ω)

HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

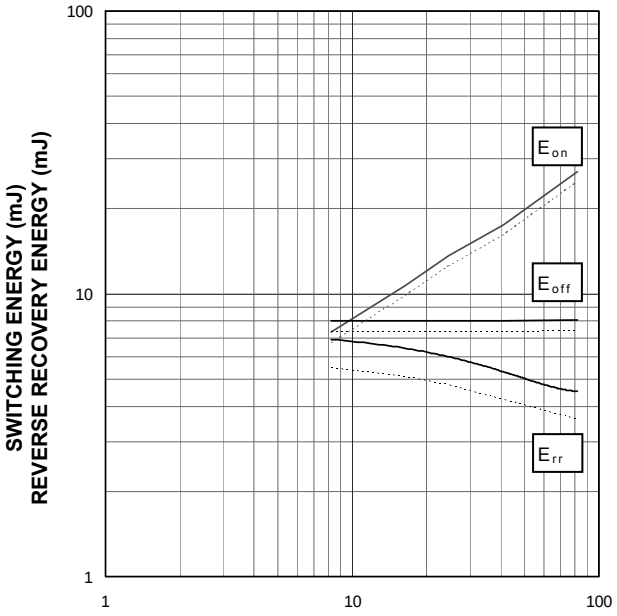
V_{CC}=600 V, V_{GE}=±15 V, R_G=8.2 Ω,
——————: T_j=150 °C, - - - - -: T_j=125 °C



COLLECTOR CURRENT I_C (A)
EMITTER CURRENT I_E (A)

HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

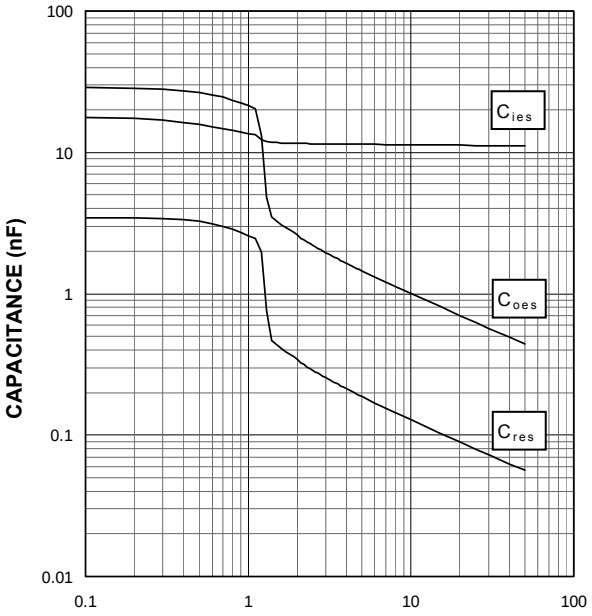
V_{CC}=600 V, V_{GE}=±15 V, I_C=75 A,
——————: T_j=150 °C, - - - - -: T_j=125 °C



EXTERNAL GATE RESISTANCE R_G (Ω)

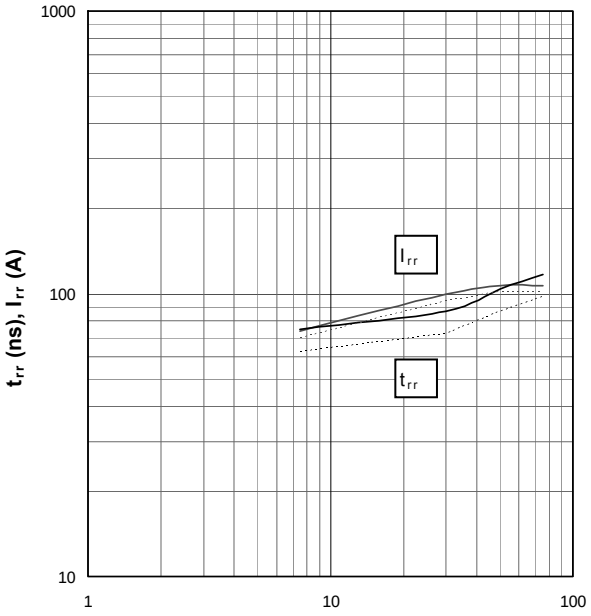
CAPACITANCE CHARACTERISTICS (TYPICAL)

G-E short-circuited, T_j=25 °C



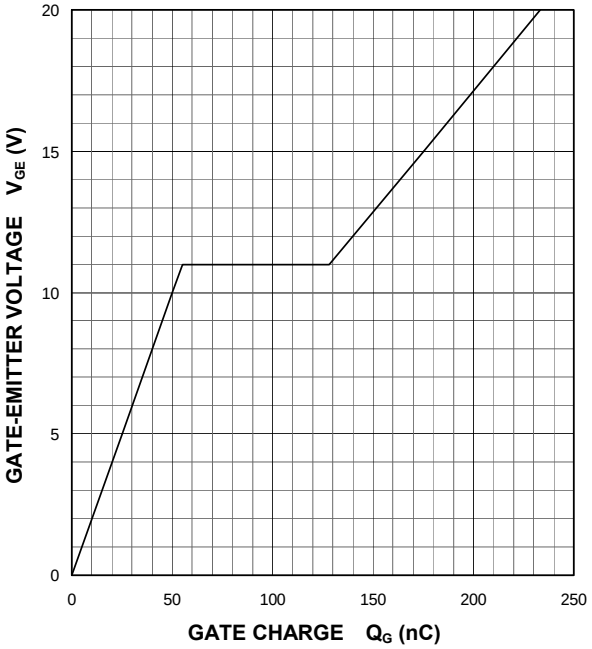
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

V_{CC}=600 V, V_{GE}=±15 V, R_G=8.2 Ω,
——: T_j=150 °C, - - - - -: T_j=125 °C



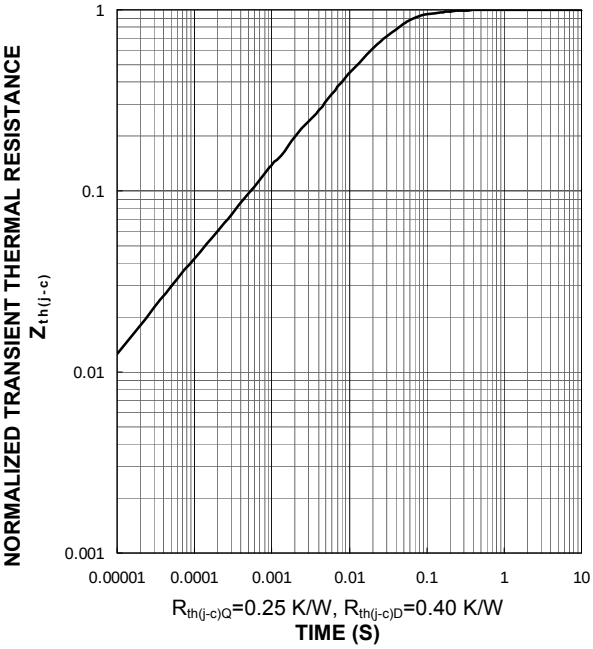
GATE CHARGE CHARACTERISTICS (TYPICAL)

V_{CC}=600 V, I_C=75 A, T_j=25 °C



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

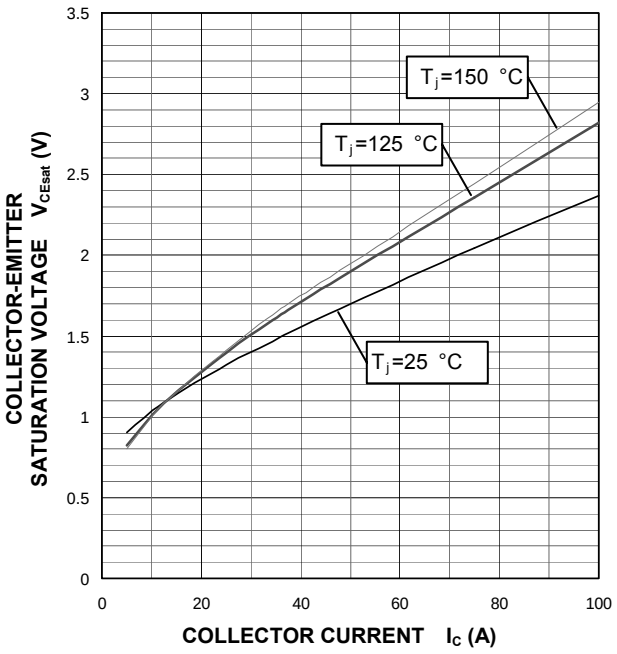
Single pulse, T_C=25 °C



BRAKE PART

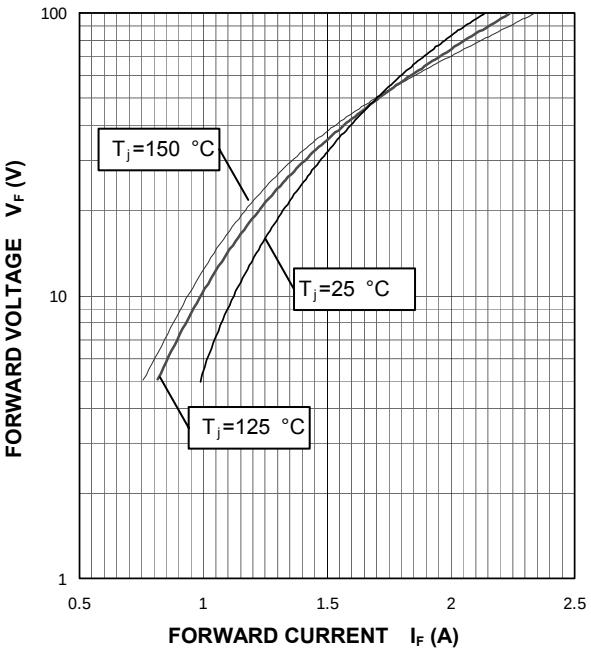
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

V_{GE}=15 V (Chip)



CLAMP DIODE FORWARD CHARACTERISTICS (TYPICAL)

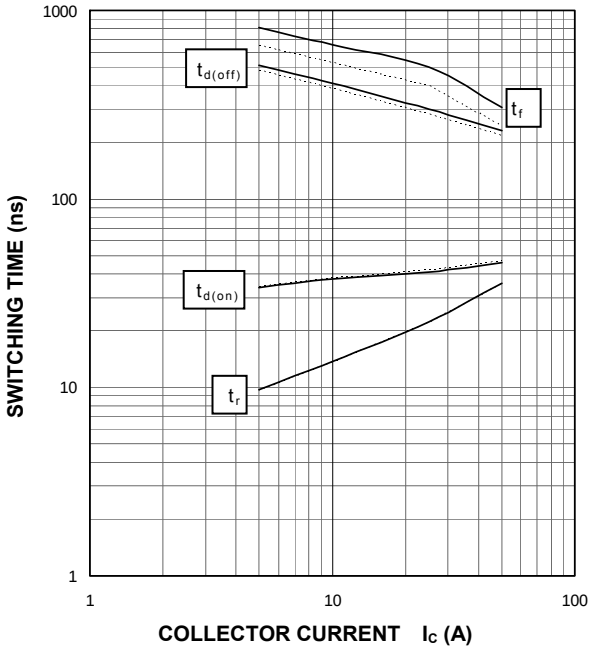
G-E short-circuited (Chip)



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=600 V, V_{GE}=±15 V, R_G=13 Ω, INDUCTIVE LOAD

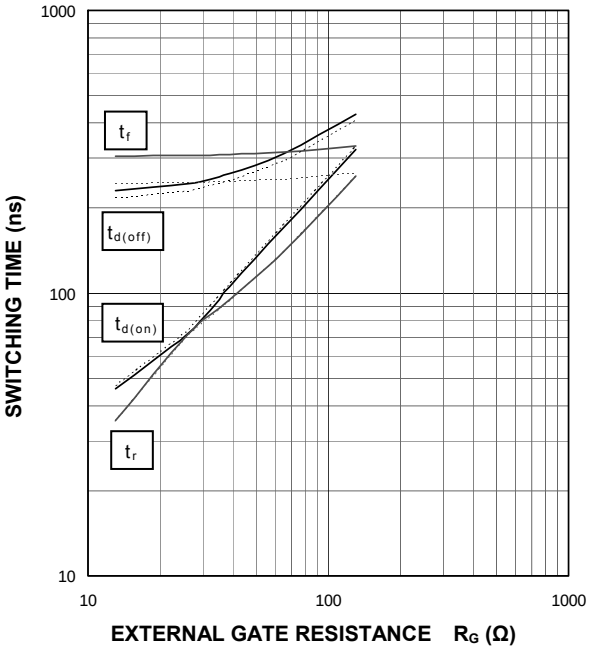
————: T_j=150 °C, - - - - -: T_j=125 °C



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

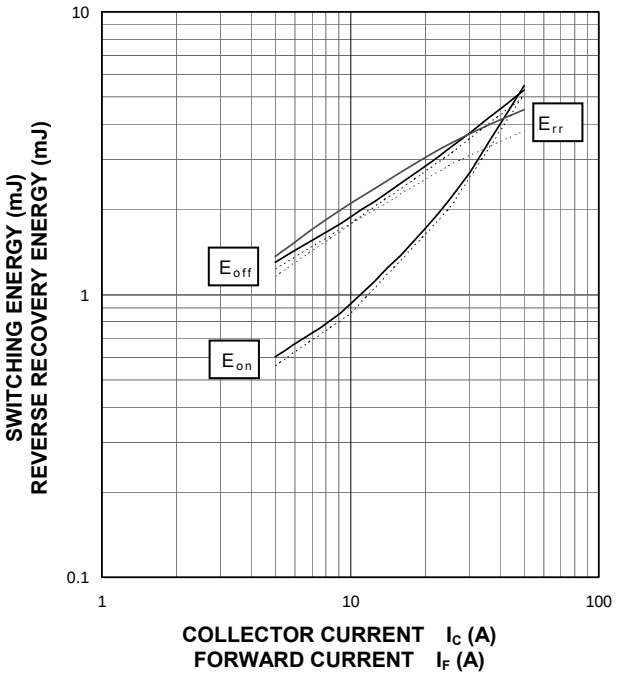
V_{CC}=600 V, I_C=50 A, V_{GE}=±15 V, INDUCTIVE LOAD

————: T_j=150 °C, - - - - -: T_j=125 °C



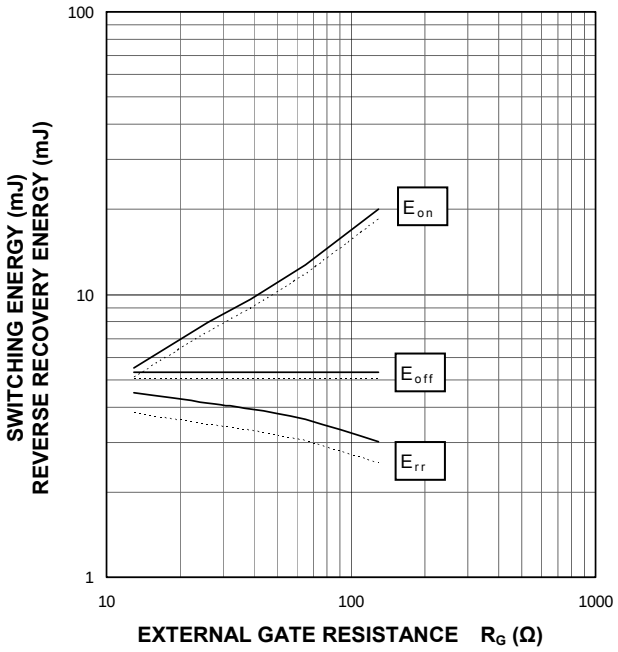
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

V_{CC}=600 V, V_{GE}=±15 V, R_G=13 Ω,
INDUCTIVE LOAD, PER PULSE
————: T_j=150 °C, - - - - -: T_j=125 °C



HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

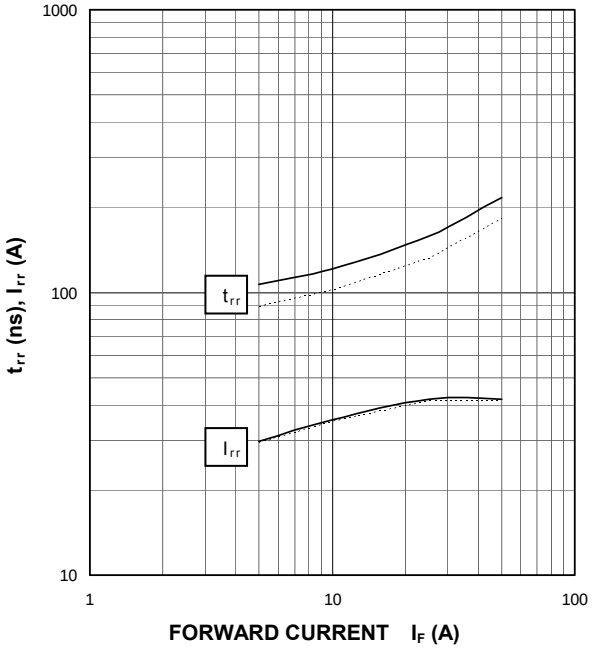
V_{CC}=600 V, I_C/I_F=50 A, V_{GE}=±15 V,
INDUCTIVE LOAD, PER PULSE
————: T_j=150 °C, - - - - -: T_j=125 °C



CONVERTER PART

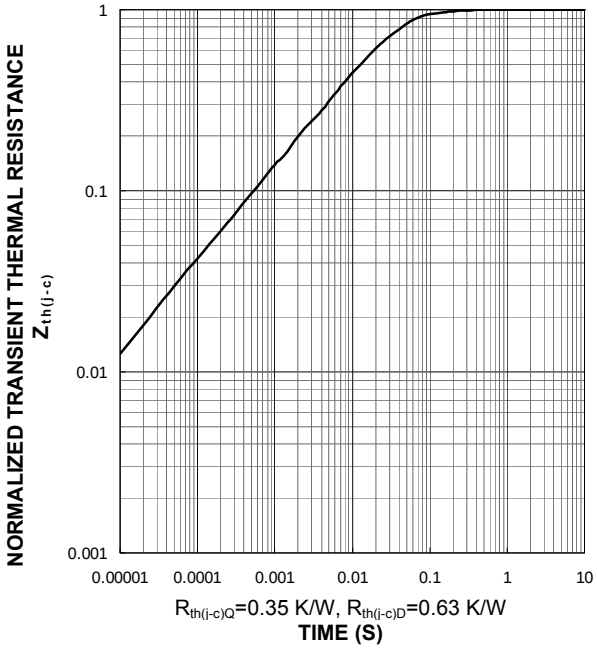
CLAMP DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)

V_{CC}=600 V, V_{GE}=±15 V, R_G=13 Ω, INDUCTIVE LOAD
————: T_j=150 °C, - - - - -: T_j=125 °C



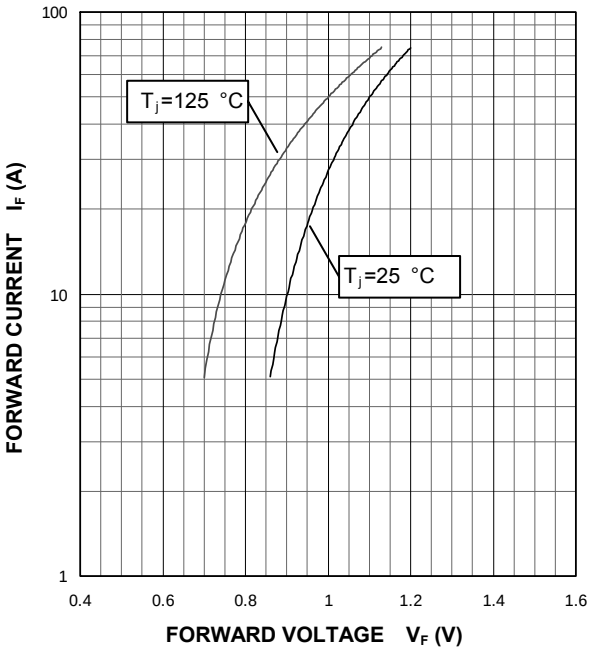
TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS
(MAXIMUM)

Single pulse, T_C=25 °C



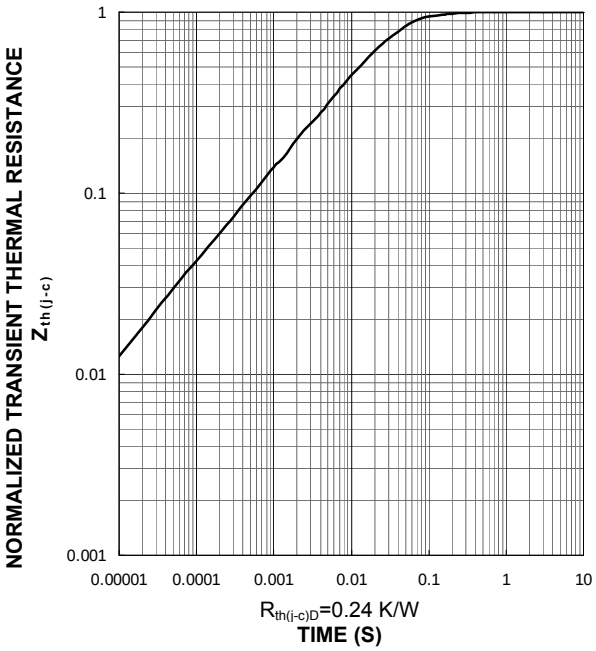
CONVERTER PART

CONVERTER DIODE FORWARD CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

Single pulse, T_C=25 °C



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